



40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C (Note 10)
40\/	2.5mΩ @ V _{GS} = 10V	100A
40V	5mΩ @ V _{GS} = 4.5V	100A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

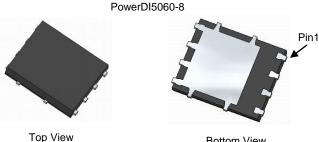
- **Engine Management Systems**
- **Body Control Electronics**
- DC-DC Converters

Features

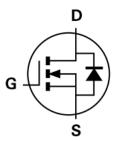
- Rated to +175°C Ideal for High Ambient Temperature **Environments**
- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Qg Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Bottom View



Internal Schematic

D D s [GΓ Пο Top View

Pin Configuration

Пп

Ordering Information (Note 5)

Part Number	Case	Packaging
DMTH4004LPSQ-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



);; = Manufacturer's Marking TH4004LSQ = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018)WW = Week (01 to 53)

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Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Notes 7 & 10)	T _C = +25°C	I _D	100	А
Continuous Drain Current (Notes 7 & 10)	T _C = +100°C		100	
Maximum Continuous Body Diode Forward Current (Note 7)	I _S	100	Α	
Pulsed Drain Current (380μs Pulse, Duty Cycle = 1%)		I _{DM}	400	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	400	Α
Avalanche Current, L=0.2mH		I _{AS}	53.2	Α
Avalanche Energy, L=0.2mH		E _{AS}	283	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	$T_A = +25$ °C	P_{D}	2.83	W
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	53	°C/W
Total Power Dissipation (Note 7)	$T_C = +25^{\circ}C$	P_D	125	W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	1.2	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +175	°C

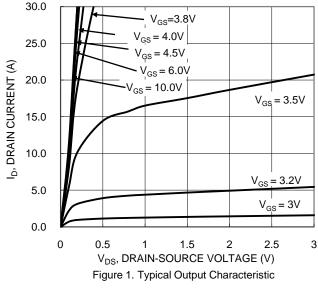
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	•						
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	2.14	2.5	mΩ	$V_{GS} = 10V, I_D = 50A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	3.85	5	11112	$V_{GS} = 4.5V, I_D = 50A$	
Diode Forward Voltage	V _{SD}	_	0.85	1.2	V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	5220	_			
Output Capacitance	Coss	_	1734	_	pF	$V_{DS} = 20V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	79	_		I = IIVINZ	
Gate Resistance	Rg	_	0.59	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	32.4	_	nC		
Total Gate Charge (V _{GS} = 10V)	Qg	_	69.6	_	N/ 001/ 1 00 A		
Gate-Source Charge	Q _{gs}	_	13	_	nC	$V_{DD} = 20V, I_D = 30A$	
Gate-Drain Charge	Q _{gd}	_	14.7	_			
Turn-On Delay Time	t _{D(ON)}	_	9.0	_			
Turn-On Rise Time	t _R	_	10.4	_		$V_{DD} = 20V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	24.4	_	ns	$I_D = 30A, R_g = 1.6\Omega$	
Turn-Off Fall Time	t _F	_	6.0	_		_	
Body Diode Reverse Recovery Time	t _{RR}	_	54.3	_	ns	1 FOA di/dt 100A/uc	
Body Diode Reverse Recovery Charge	Q _{RR}	_	89.5	_	nC	$I_F = 50A$, di/dt = 100A/ μ s	

Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad). 8 .Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to production testing.
- 10. Limited by package.





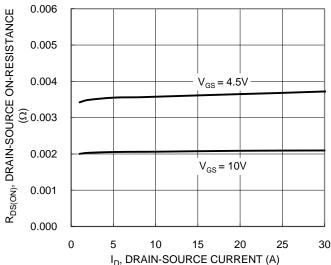


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

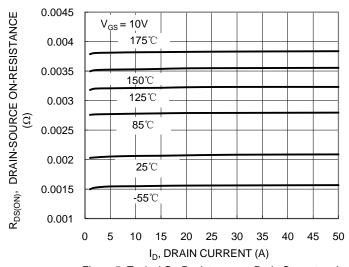


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

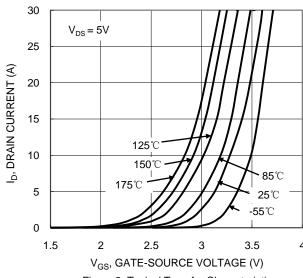
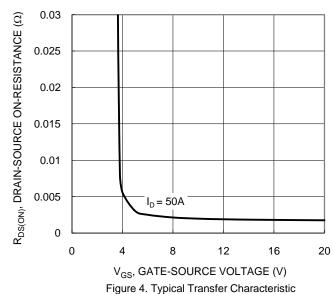


Figure 2. Typical Transfer Characteristic



2.4 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 2.2 2 $V_{GS} = 10V, I_{D} = 50A$ 1.8 1.6 1.4 1.2 1 $V_{GS} = 4.5V, I_D = 50A$ 8.0 0.6 0.4 -50 -25 0 25 50 75 100 125 150 175 T_J, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Temperature



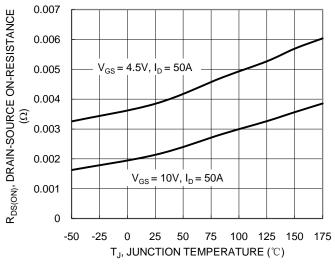
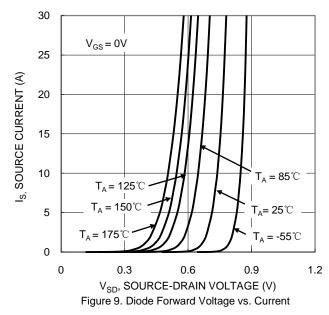
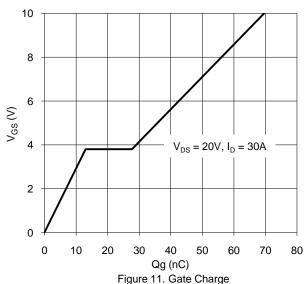


Figure 7. On-Resistance Variation with Temperature





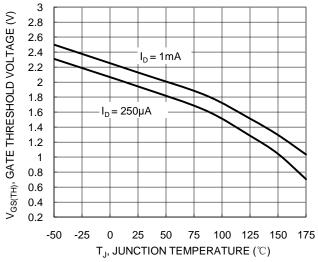
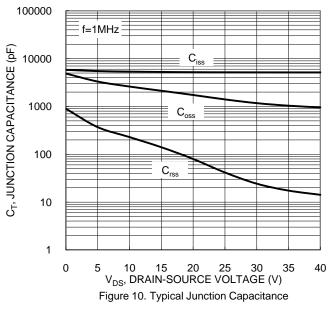


Figure 8. Gate Threshold Variation vs. Junction Temperature



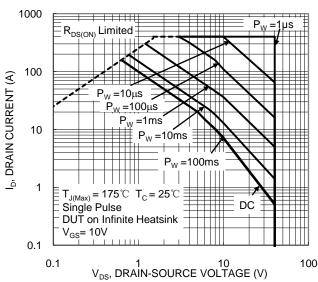


Figure 12. SOA, Safe Operation Area



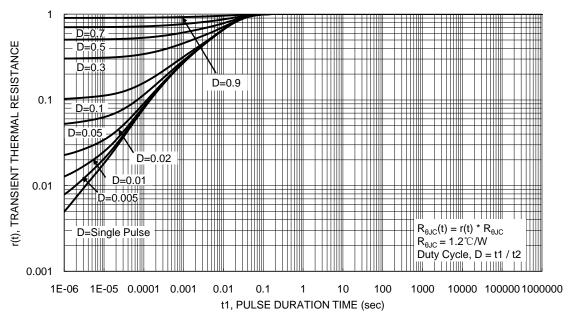


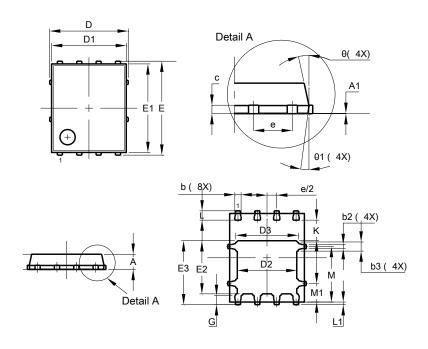
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

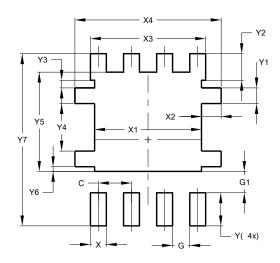


PowerDI5060-8					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	,	5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е		6.15 BSC			
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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